

Homework R. Martin

Problem 8.1a

For $V_{DD} = 1.3$ V and using $I_{REF} = 100$ uA, it is required to design the circuit of Fig. 8.1 to obtain an output current whose nominal value is 100 uA. Find R if Q_1 and Q_2 are matched with channel lengths of 0.5 um, channel widths of 5 um, $V_t =$ 0.4 V, and $k'_n = 500 \text{ uA/V}^2$. What is the lowest possible value of V_0 ? Assuming that for this process technology the Early voltage $V'_A = 5$ V/um, find the output resistance of the current source. Also, find the change in output current resulting

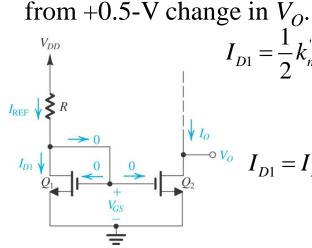


Figure 8.1 Circuit for a basic MOSFET constant-current source. For proper operation, the output terminal, that is, the drain of Q_2 , must be connected to a circuit that ensures that Q_2 operates in saturation.

Homework

$$I_{D1} = \frac{1}{2}k_n' \left(\frac{W}{L}\right)_1 V_{OV}^2 \qquad V_{OV} = \sqrt{\frac{2I_{D1}}{k_n' \left(\frac{W}{L}\right)_1}} = \sqrt{\frac{2 \times 0.1 \text{mA}}{500 \frac{\text{uA}}{\text{V}^2} \times \frac{5 \text{um}}{0.5 \text{um}}}} = 0.2 \text{V}$$

$$I_{D1} = I_{REF} = \frac{V_{DD} - V_{GS}}{R} = \frac{V_{DD} - V_{OV} - V_{t}}{R} = \frac{1.3 - 0.2 - 0.4V}{R} = \frac{0.7V}{R}$$

$$R = \frac{0.7 \text{V}}{0.1 \text{mA}} = 7 \text{k}\Omega \qquad \text{I}$$

 $R = \frac{0.7 \text{V}}{\Omega \text{ Im} \Delta} = 7 \text{k}\Omega$ Lowest value of V_o is when V_{DS} of $Q_2 = V_{QV} = 0.2V$

Problem 8.1b

For $V_{DD} = 1.3$ V and using $I_{REF} = 100$ uA, it is required to design the circuit of Fig. 8.1 to obtain an output current whose nominal value is 100 uA. Find R if Q_1 and Q_2 are matched with channel lengths of 0.5 um, channel widths of 5 um, $V_t = 0.5$ V, and $k'_n = 500$ uA/V². What is the lowest possible value of V_O ? Assuming that for this process technology the Early voltage $V'_A = 5$ V/um, find the output resistance of the current source. Also, find the change in output current resulting from +0.5-V change in V_O .

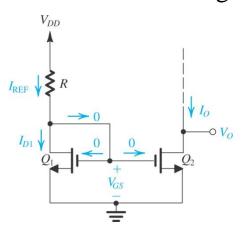


Figure 8.1 Circuit for a basic MOSFET constant-current source. For proper operation, the output terminal, that is, the drain of Q_2 , must be connected to a circuit that ensures that Q_2 operates in saturation.

Homework

$$r_o = \frac{V_A}{I_D} = \frac{V_A'L}{I_D} = \frac{5V_{um} \times 0.5 \text{um}}{0.1 \text{mA}} = 25 \text{k}\Omega$$

$$\Delta V_o = \Delta I_o \times r_0$$

$$\Delta I_o = \frac{\Delta V_o}{r_0} = \frac{0.5 \text{V}}{25 \text{k}\Omega} = 0.02 \text{mA}$$

R. Martin

Problem 8.5

For the current-steering circuit of Fig. P8.5, find I_o in terms of I_{REF} and device W/L ratios.

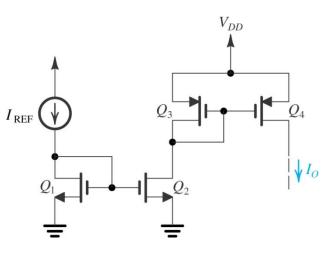


Figure P8.5

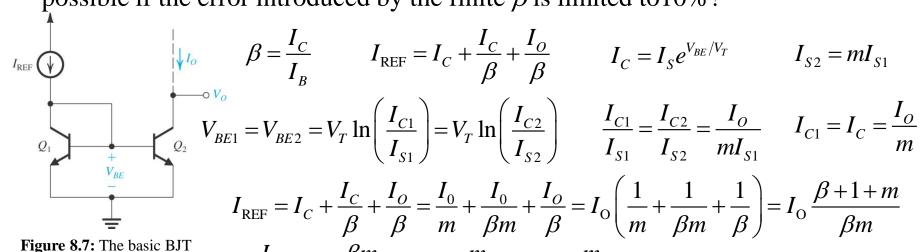
$$rac{I_{Q2}}{I_{Q1}} = rac{ig(W/Lig)_2}{ig(W/Lig)_1} \qquad \qquad rac{I_{Q4}}{I_{Q3}} = rac{ig(W/Lig)_4}{ig(W/Lig)_3}$$

$$I_{Q1} = I_{\rm REF}$$
 , $I_{Q3} = I_{Q2}$ and $I_{O} = I_{Q4}$

$$\frac{I_{O}}{I_{REF}} = \frac{I_{Q4}}{I_{Q1}} = \frac{I_{Q3} \left(\frac{(W/L)_{4}}{(W/L)_{3}}\right)}{I_{Q2} \left(\frac{(W/L)_{1}}{(W/L)_{2}}\right)} = \frac{(W/L)_{2} (W/L)_{4}}{(W/L)_{1} (W/L)_{3}}$$

Problem 8.9a

Consider the basic BJT current mirror of Fig. 8.7 for the case in which Q_2 has m times the area of Q_1 . Show that the current transfer ratio is given by Eq. (8.19). If β is specified to be a minimum of 80, what is the largest current transfer ratio possible if the error introduced by the finite β is limited to 10%?



$$\begin{split} I_{\text{REF}} &= I_C + \frac{I_C}{\beta} + \frac{I_O}{\beta} = \frac{I_0}{m} + \frac{I_0}{\beta m} + \frac{I_O}{\beta} = I_O \left(\frac{1}{m} + \frac{1}{\beta m} + \frac{1}{\beta} \right) = I_O \frac{\beta + 1 + m}{\beta m} \\ \frac{I_O}{I_{\text{REF}}} &= \frac{\beta m}{\beta + 1 + m} = \frac{m}{1 + \frac{1}{O} + \frac{m}{O}} = \frac{m}{1 + \frac{m+1}{O}} \end{split}$$

current mirror. Eq. (8.19)

$$\frac{I_O}{I_{\text{REF}}} = \frac{1}{\left(1 + \frac{2}{\beta}\right)}$$

If the transistors are identical (matched) then m = 1 and we arrive at equation 8.19.

Problem 8.9b

Consider the basic BJT current mirror of Fig. 8.7 for the case in which Q_2 has m times the area of Q_1 . Show that the current transfer ratio is given by Eq. (8.19). If β is specified to be a minimum of 80, what is the largest current transfer ratio possible if the error introduced by the finite β is limited to 10%?

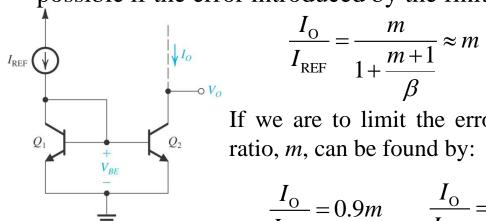


Figure 8.7: The basic BJT current mirror.

Eq. (8.19)
$$\frac{I_O}{I_{\text{REF}}} = \frac{1}{\left(1 + \frac{2}{\beta}\right)}$$

$$\frac{I_{\rm O}}{I_{\rm REF}} = \frac{m}{1 + \frac{m+1}{\beta}} \approx m$$

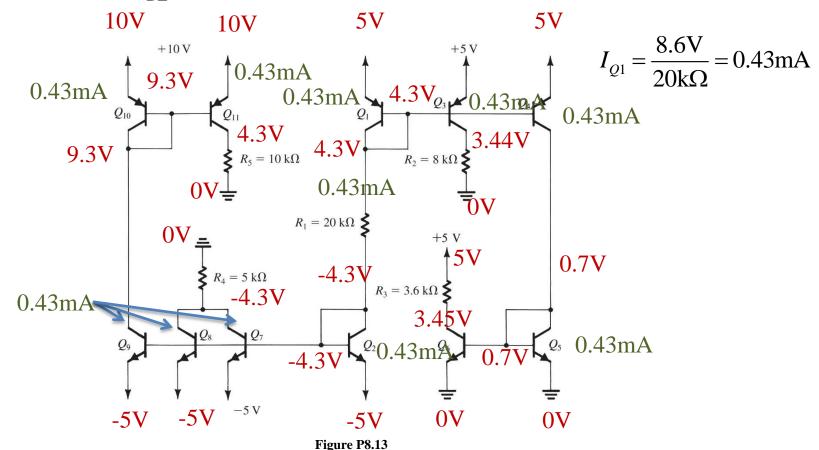
If we are to limit the error to 10% then the maximum current transfer ratio, m, can be found by:

$$\frac{I_{\rm O}}{I_{\rm REF}} = 0.9m$$
 $\frac{I_{\rm O}}{I_{\rm REF}} = 0.9m = \frac{m}{1 + \frac{m+1}{\beta}}$

$$\frac{I_O}{I_{REF}} = \frac{1}{\left(1 + \frac{2}{B}\right)} \qquad 0.9 = \frac{1}{1 + \frac{m+1}{80}} = \frac{80}{80 + 1 + m} = \frac{80}{81 + m} \qquad m = 7.888$$

Problem 8.13

Find the voltages at all nodes and the currents through all branches in the circuit of Fig. P8.13. Assume $|V_{BE}| = 0.7$ V and $\beta = \infty$.



R. Martin

Homework

Problem 8.14

For the circuit in Fig. P8.14, let $|V_{BE}| = 0.7$ V and $\beta = \infty$. Find I, V_1 , V_2 , V_3 , V_4 , and V_5 for (a) R = 10 k Ω and (b) R = 100 k Ω .

$$V_{1} = V_{B1} - V_{BE1} = 0 \text{V} - 0.7 \text{V} = -0.7 \text{V}$$

$$I_{Q1} = \frac{V_{1} - V_{EE}}{R} = \frac{-0.7 \text{V} + 2.7 \text{V}}{R} = \frac{2 \text{V}}{R}$$

$$I = 2I_{Q1} = (2) \frac{2 \text{V}}{R}$$

$$V_{2} = V_{CC} - V_{EB} = 2.7 \text{V} - 0.7 \text{V} = 2.0 \text{V}$$

$$V_{3} = V_{B6} - V_{EB6} = 0 \text{V} + 0.7 \text{V} = 0.7 \text{V}$$

$$V_{4} = V_{EE} + \left(\frac{I}{2}\right) R = -2.7 \text{V} + \frac{2 \text{V}}{R} R = -0.7 \text{V}$$

$$V_{5} = V_{EE} + \left(\frac{I}{2}\right) \frac{R}{2} = -2.7 \text{V} + \frac{2 \text{V}}{R} \frac{R}{2} = -1.7 \text{V}$$
Figure P8.14

R. Martin

Problem 8.17

The MOSFETs in the current mirror of Fig.8.12 (a) have equal channel lengths of 0.5 μ m, $W_1 = 10 \mu$ m, $W_2 = 50 \mu$ m, $\mu_n C_{ox} = 500 \mu$ A/V², and V'_A = 10 V/ μ m. If the input bias current is 100 μ A, find R_{in} , A_{is} , and R_o .

$$r_{o1} = \frac{V_A}{I_{D1}} = \frac{V_A'L}{I_{D1}} = \frac{10\frac{V}{\mu m}0.5\mu m}{0.1 mA} = 50k\Omega$$

$$g_{m1} = \sqrt{2\mu_n C_{ox}} \left(\frac{W}{L}\right)_1 I_{D1} = \sqrt{2 \times 0.5 \frac{mA}{V^2} \left(\frac{10}{0.5}\right)_1 0.1 mA} = 1.414 mA/V$$

$$R_{in} = r_{o1} || \frac{1}{g_{m1}} = 50k\Omega || \frac{1}{1.414} = 50k\Omega || 707\Omega = 697\Omega$$

$$A_{is} = \frac{(W/L)_{2}}{(W/L)_{1}} = 5\frac{A}{A} \implies I_{D2} = A_{is}I_{D1} = 5\frac{A}{A}0.1\text{mA} = 0.5\text{mA}$$

$$R_{o} = r_{o2} = \frac{V_{A2}}{I_{D2}} = \frac{10\frac{V}{\mu\text{m}}0.5\mu\text{m}}{0.5\text{mA}} = 10\text{k}\Omega$$

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